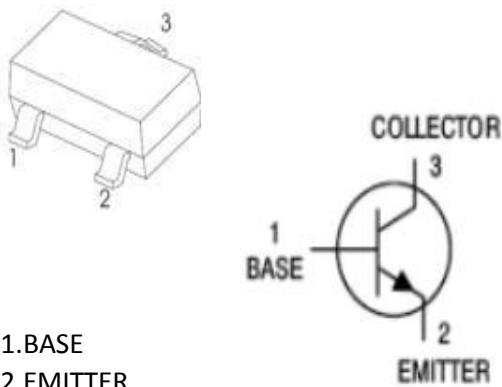


TRANSI STOR (NPN)	SOT-23 Plastic-Encapsulate Transistors																																				
<u>SOT-23</u>  1.BASE 2.EMITTER 3.COLLECTOR Marking :G1	Features ※ Complimentary to MMBT5401 ※ Collector Current: Ic=0.6A ※ Ideal for Medium Power Amplification and Switching																																				
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted) <table><tr><th>Parameter</th><th>Symbol</th><th>Value</th><th>Unit</th></tr><tr><td>Collector-Base Voltage</td><td>VCBO</td><td>180</td><td>V</td></tr><tr><td>Collector-Emitter Voltage</td><td>VCEO</td><td>160</td><td>V</td></tr><tr><td>Emitter-Base Voltage</td><td>VEBO</td><td>6</td><td>V</td></tr><tr><td>Collector Current</td><td>IC</td><td>600</td><td>mA</td></tr><tr><td>Collector Power Dissipation</td><td>PC</td><td>300</td><td>mW</td></tr><tr><td>Thermal Resistance From Junction To Ambient</td><td>RθJA</td><td>416</td><td>℃/W</td></tr><tr><td>Junction Temperature</td><td>Tj</td><td>150</td><td>℃</td></tr><tr><td>Storage Temperature</td><td>Tstg</td><td>-55~+150</td><td>℃</td></tr></table>		Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	180	V	Collector-Emitter Voltage	VCEO	160	V	Emitter-Base Voltage	VEBO	6	V	Collector Current	IC	600	mA	Collector Power Dissipation	PC	300	mW	Thermal Resistance From Junction To Ambient	RθJA	416	℃/W	Junction Temperature	Tj	150	℃	Storage Temperature	Tstg	-55~+150	℃
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ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	180			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	160			V
Emitter-base breakdown voltage	V(BR)EBO	IE= 10μA, IC=0	6			V
Collector cut-off current	ICBO	VCB= 120 V , IE=0			50	nA
Collector cut-off current	ICEO	VCE= 120V , IB=0			0.8	μA
Emitter cut-off current	IEBO	VEB= 4V , IC=0			50	nA
DC current gain	hFE	VCE=5V, IC= 1mA	80			
	hFE	VCE=5V, IC= 10mA	100		300	
	hFE	VCE=5V, IC= 50mA	50			
Collector-emitter saturation voltage	VCE(sat)	IC=10 mA, IB= 1mA			0.15	V
Base-emitter saturation voltage	VBE(sat)	IC=50 mA, IB= 5mA			1	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	100		300	MHz
Collector Current Capacitance	Cod	VCB= 10V, IE=0, f=1MHz			6	pF

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

